BORN SEMICONDUCTOR

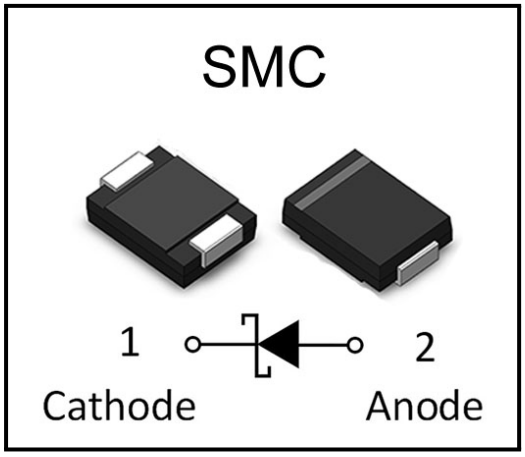
SS82-SS820

Schottky Barrier Diode

Features

- For surface mounted applications
- Matal silicon junction,majority carrier conduction
- Low power loss,high efficiency
- Buit-in strain relief,ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed: 250°C/10 seconds at terminals

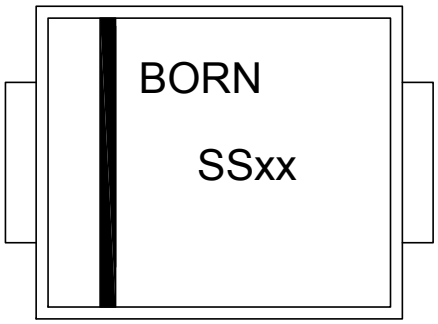
Package



Description

- Case: JEDEC DO-214AB molded plastic
- Terminals:Axial leads.Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode
- Mounting Position:Any

Marking



Ordering information

Part Number	SS82	SS84	SS86	SS88	SS810	SS815	SS820
Marking	SS82	SS84	SS86	SS88	SS810	SS815	SS820
Base qty	3K	3K	3K	3K	3K	3K	3K

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Revision: 2022-Jan-1-A

SS82-SS820

Schottky Barrier Diode

Maximum Ratings and Electrical Characteristics@T_A=25°C unless otherwise noted

Symbol	Parameters	SS82	SS84	SS86	SS88	SS810	SS815	SS820	Units
V_{RRM}	Maximum Repetitive Peak Reverse Voltage	20	40	60	80	100	150	200	V
V_{RMS}	Maximum RMS Voltage	14	21	28	56	70	105	150	V
V_{DC}	Maximum DC Blocking Voltage	20	40	60	80	100	150	200	V
$I_{F(AV)}$	Maximum average forward Rectified Current	8.0							A
I_{FSM}	Non-repetitive peak forward surge current 8.3 ms singlehalf sine-wave	120							A
V_F	Maximum Instantaneous Forward Voltage at 8.0A	0.55		0.70	0.85		0.95		V
I_R	Maximum DC Reverse current T_A=25°C	0.2			0.1				mA
	at Rated DC Blocking Voltage T_A=100°C	20			5.0				
C_j	Typical junction capacitance	450		350	270		180		pF
T_J	Operating Temperature Range	-55 to +150							°C
T_{STG}	Storage Temperature Range	-55 to +150							°C
$R_{\theta JA}$	Thermal Resistance(1)	45							°C/W
$R_{\theta JL}$		12							

Note:(1) Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.6” x 0.6” (16 mm x 16 mm) copper pad areas.

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SS82-SS820

Schottky Barrier Diode

Typical Performance Characteristics(T_J = 25 °C, unless otherwise noted)

Figure 1:I_O-T_L Curve

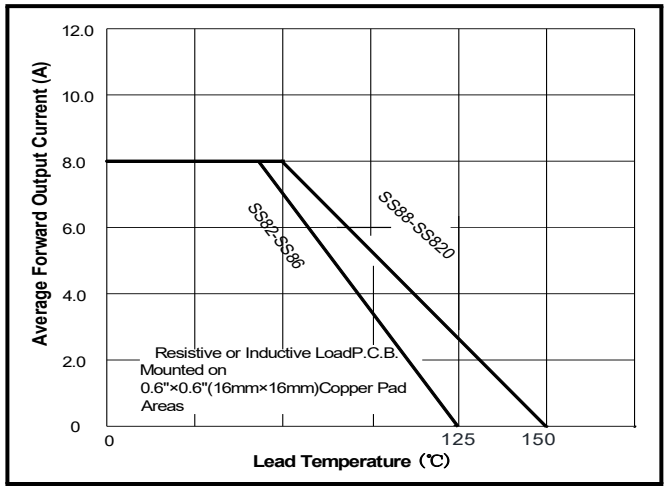


Figure 2:Forward Surge Current Capability

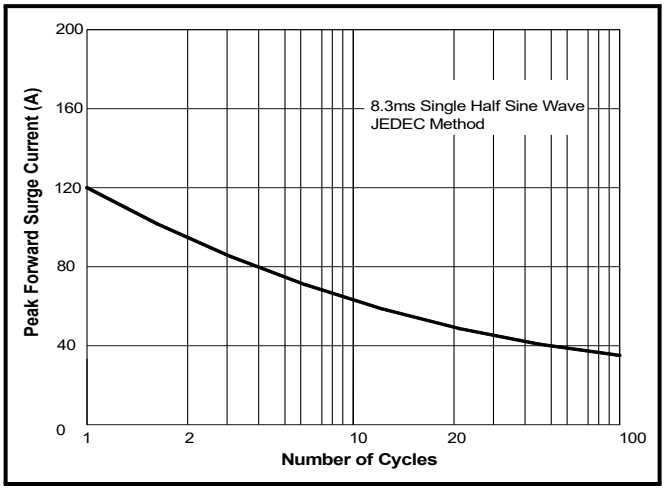


Figure 3: Forward Voltage

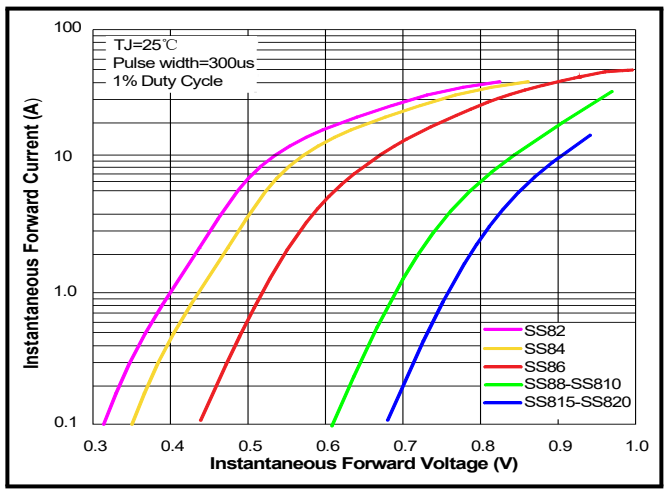
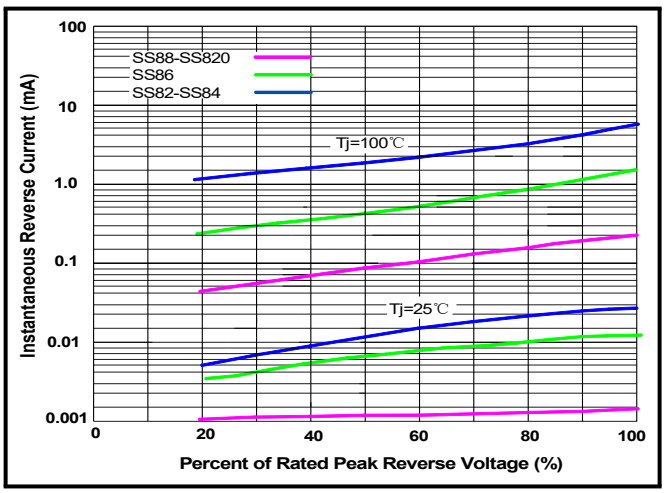


Figure 4:Typical Reverse Characteristics



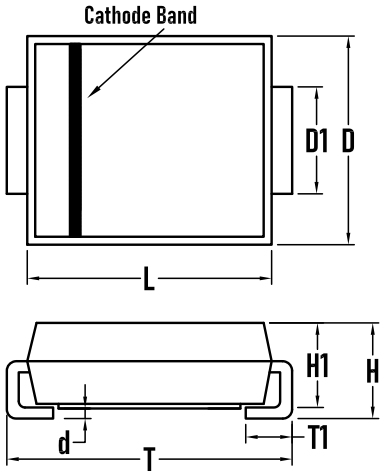
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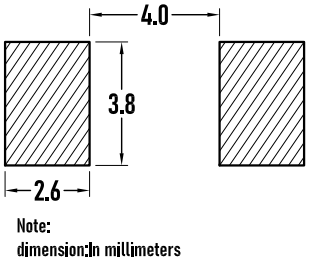
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SS82-SS820

Schottky Barrier Diode

Package Mechanical Data - SMC

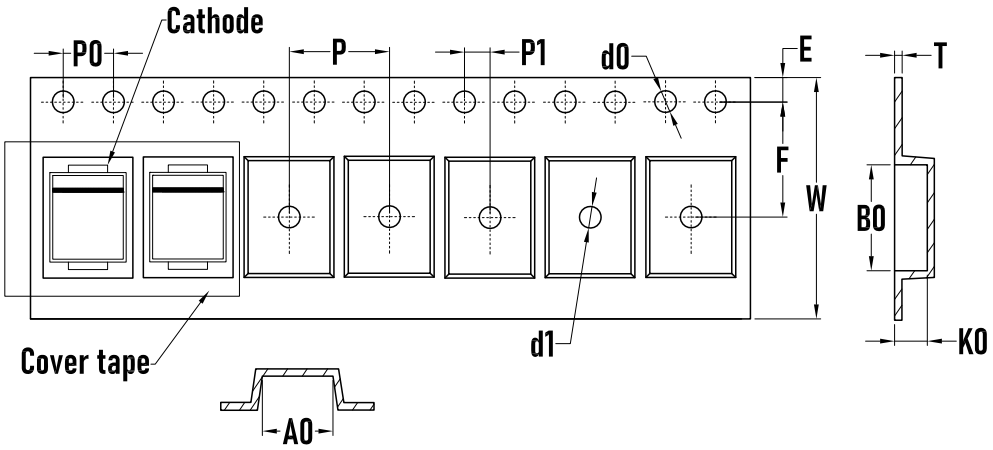




Note:
dimension:In millimeters

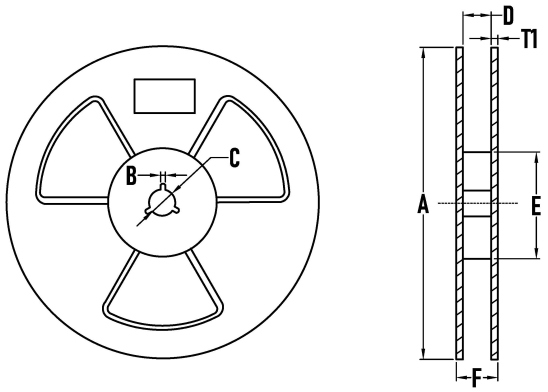
SYMBOL	MILLIMETER		Inches	
	MIN	MAX	MIN	MAX
D	5.5	6.1	0.217	0.240
D1	2.7	3.3	0.106	0.130
T	7.4	8.4	0.291	0.331
T1	0.8	1.6	0.031	0.063
d	–	0.3	–	0.012
H1	2.0	2.6	0.079	0.102
H	2.1	2.7	0.083	0.106
L	6.5	7.1	0.256	0.280

Packaging Tape - SMC



SYMBOL	MILLIMETER
A0	6.00±0.1
B0	8.25±0.02
d0	1.50±0.1
d1	1.50±0.1
E	1.75±0.1
F	7.50±0.1
K0	2.70±0.1
P	8.00±0.1
P0	4.00±0.1
P1	2.00±0.05
W	16.00±0.1
T	0.22±0.02

Packaging Reel



SYMBOL	MILLIMETER
A	323±2
B	3.0±0.2
C	15.0±0.5
D	16±2
E	73±2
T1	2.2±0.2
Quantity	3000PCS

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